Abstracts

A Broadband Low Noise Dual Gate FET Distributed Amplifier

W.J. Thompson. "A Broadband Low Noise Dual Gate FET Distributed Amplifier." 1989 Microwave and Millimeter-Wave Monolithic Circuits Symposium Digest 89.1 (1989 [MCS]): 11-13.

A 2 to 18 GHz monolithic GaAs low noise distributed amplifier has been developed with 10 dB nominal gain. The noise figure is less than 5.7 dB over the 2 to 18 GHz band and less than 4.0 dB from 3 to 13 GHz. The DGFET amplifier provides gain control capability and has low power requirements of 60 mA at 5 volts. This state of the art performance is achieved with a 0.5 µM ion implanted process.

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